

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1129	defects same silicon same copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 12:26
S2	28	electrolyte and bath and S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:00
S3	99	d-defects	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:35
S4	62	copper and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:36
S5	2	(electro or electrolyte) and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:36
S6	1	("5783495").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/02 08:37
S7	8	("5980720").URPN.	USPAT	OR	ON	2005/03/02 08:39
S8	32919	(slot or slots) and copper	USPAT	OR	ON	2005/03/02 08:43
S9	0	S3 and S8	USPAT	OR	ON	2005/03/02 08:41
S10	1121	copper adj bath	USPAT	OR	ON	2005/03/02 08:42
S11	818	(wafer or substrate) and S10	USPAT	OR	ON	2005/03/02 08:42
S12	47	(slot or slots) and S11	USPAT	OR	ON	2005/03/02 08:43
S13	29	("3716462").URPN.	USPAT	OR	ON	2005/03/02 09:34
S14	4108	kim.in. and copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 10:48

S15	23	decoration and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 10:53
S16	1740	(438/14).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 10:54
S17	22	(438/441).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 12:23
S18	1412	(438/687).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 12:26
S19	232	(electrolyte or electrolytic or electrodeless) and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 12:27

<u>NEWS</u>	<u>1</u>	Web Page URLs for STN Seminar Schedule - N. America
<u>NEWS</u>	<u>2</u>	"Ask CAS" for self-help around the clock
<u>NEWS</u>	<u>3</u>	SEP 01 New pricing for the Save Answers for SciFinder Wizard within STN Express with Discover!
<u>NEWS</u>	<u>4</u>	OCT 28 KOREAPAT now available on STN
<u>NEWS</u>	<u>5</u>	NOV. 30 PHAR reloaded with additional data
<u>NEWS</u>	<u>6</u>	DEC 01 LISA now available on STN
<u>NEWS</u>	<u>7</u>	DEC 09 12 databases to be removed from STN on December 31, 2004
<u>NEWS</u>	<u>8</u>	DEC 15 MEDLINE update schedule for December 2004
<u>NEWS</u>	<u>9</u>	DEC 17 ELCOM reloaded; updating to resume; current-awareness alerts (SDIs) affected
<u>NEWS</u>	<u>10</u>	DEC 17 COMPUAB reloaded; updating to resume; current-awareness alerts (SDIs) affected
<u>NEWS</u>	<u>11</u>	DEC 17 SOLIDSTATE reloaded; updating to resume; current-awareness alerts (SDIs) affected
<u>NEWS</u>	<u>12</u>	DEC 17 CERAB reloaded; updating to resume; current-awareness alerts (SDIs) affected
<u>NEWS</u>	<u>13</u>	DEC 17 THREE NEW FIELDS ADDED TO IFIPAT/IFIUDB/IFICDB
<u>NEWS</u>	<u>14</u>	DEC 30 EPFULL: New patent full text database to be available on STN
<u>NEWS</u>	<u>15</u>	DEC 30 CAPLUS - PATENT COVERAGE EXPANDED
<u>NEWS</u>	<u>16</u>	JAN 03 No connect-hour charges in EPFULL during January and February 2005
<u>NEWS</u>	<u>17</u>	FEB 25 CA/CAPLUS - Russian Agency for Patents and Trademarks (ROSPATENT) added to list of core patent offices covered
<u>NEWS</u>	<u>18</u>	FEB 10 STN Patent Forums to be held in March 2005
<u>NEWS</u>	<u>19</u>	FEB 16 STN User Update to be held in conjunction with the 229th ACS National Meeting on March 13, 2005
<u>NEWS</u>	<u>20</u>	FEB 28 PATDPAFULL - New display fields provide for legal status data from INPADOC
<u>NEWS</u>	<u>21</u>	FEB 28 BABS - Current-awareness alerts (SDIs) available
<u>NEWS</u>	<u>22</u>	FEB 28 MEDLINE/LMEDLINE reloaded

NEWS EXPRESS JANUARY 10 CURRENT WINDOWS VERSION IS V7.01a, CURRENT MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP), AND CURRENT DISCOVER FILE IS DATED 10 JANUARY 2005

<u>NEWS HOURS</u>	STN Operating Hours Plus Help Desk Availability
<u>NEWS INTER</u>	General Internet Information
<u>NEWS LOGIN</u>	Welcome Banner and News Items
<u>NEWS PHONE</u>	Direct Dial and Telecommunication Network Access to STN
<u>NEWS WWW</u>	CAS World Wide Web Site (general information)

Enter NEWS followed by the item number or name to see news on that specific topic.

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FILE 'HOME' ENTERED AT 08:26:23 ON 02 MAR 2005

=> file inspec  
COST IN U.S. DOLLARS

SINCE FILE TOTAL  
ENTRY SESSION

FULL ESTIMATED COST 0.21 0.21

FILE 'INSPEC' ENTERED AT 08:26:34 ON 02 MAR 2005  
 Compiled and produced by the IEE in association with FIZ KARLSRUHE  
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FILE LAST UPDATED: 28 FEB 2005 <20050228/UP>  
 FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN  
 THE BASIC INDEX >>>

=> s copper  
 L1 142605 COPPER

=> s silicon  
 L2 327234 SILICON

=> s defects  
 L3 116900 DEFECTS

=> s slots  
 L4 8159 SLOTS

=> s 11 and 12 and 13 and 14  
 L5 0 L1 AND L2 AND L3 AND L4

=> s copper bath  
 L6 142605 COPPER  
 12284 BATH  
 47 COPPER BATH  
 (COPPER (W) BATH)

=> s 13 and 16  
 L7 0 L3 AND L6

=> s analyzing defects  
 L8 50370 ANALYZING  
 116900 DEFECTS  
 8 ANALYZING DEFECTS  
 (ANALYZING (W) DEFECTS)

=> d 18 1-8

L8 ANSWER 1 OF 8 INSPEC (C) 2005 IEE on STN

Full	Text	Abstract	References
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AN 2004:8284130 INSPEC DN B2005-03-2550G-041  
 TI Simulation of photoresist thermal flow process with viscous flow model.  
 AU Won-Young Chung; Tai-Kyung Kim; Yero Lee (Semicond. R&D Center, Samsung Electron., Gyeonggi-Do, South Korea); Jin-Young Yoon; Hyun-Woo Kim; Young-Kwan Park; Jeong-Taek Kong  
 SO Japanese Journal of Applied Physics, Part 1 (Regular Papers, Short Notes & Review Papers) (Sept. 2004) vol.43, no.9A, p.6020-5. 13 refs.  
 Published by: Japan Soc. Appl. Phys  
 CODEN: JAPNDE ISSN: 0021-4922  
 SICI: 0021-4922(200409)43:9AL.6020:SPTF;1-I  
 DT Journal  
 TC Practical; Theoretical; Experimental  
 CY Japan

LA English

L8 ANSWER 2 OF 8 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 2004:8128784 INSPEC DN B2004-11-2550G-163  
 TI Simulation technique for the PR flow process using a new viscous flow model [photoresist].  
 AU Won-Young Chung; Tai-Kyung Kim; Jin-Young Yoon; Hyun-Woo Kim; Young-Kwan Park; Jeong-Tae Kong (Semicond. R&D Center, Samsung Electron. Co. Ltd., Gyeonggi-Do, South Korea)  
 SO Proceedings of the SPIE - The International Society for Optical Engineering (2004) vol.5376, no.1, p.975-82. 11 refs.  
 Published by: SPIE-Int. Soc. Opt. Eng  
 Price: CCCC 0277-786X/04/\$15.00  
 CODEN: PSISDG ISSN: 0277-786X  
 SICI: 0277-786X(2004)5376:1L.975:STFP;1-R  
 Conference: Advances in Resist Technology and Processing XXI. Santa Clara, CA, USA, 23-24 Feb 2004  
 DT Conference Article; Journal  
 TC Practical; Theoretical; Experimental  
 CY United States  
 LA English

L8 ANSWER 3 OF 8 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 2001:6962873 INSPEC DN A2001-15-8140N-033  
 TI The influence of crack-like defects on the tensile strength of an open-cell aluminum foam.  
 AU Andrews, E.W.; Gibson, L.J. (Dept. of Mater. Sci. & Eng., MIT, Cambridge, MA, USA)  
 SO Scripta Materialia (17 April 2001) vol.44, no.7, p.1005-10. 6 refs.  
 Doc. No.: S1359-6462(01)00673-X  
 Published by: Elsevier for Board of Directors of Acta Metall  
 Price: CCCC 1359-6462/2001/\$20.00  
 CODEN: SCRMBU ISSN: 1359-6462  
 SICI: 1359-6462(20010417)44:7L.1005:ICLD;1-G  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L8 ANSWER 4 OF 8 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1997:5587190 INSPEC DN A9713-6848-002; B9707-2530F-005  
 TI Effective KOH etching prior to modified Secco etching for analyzing defects in thin bonded silicon on insulator (SOI) wafers.  
 AU Mitani, K.; Aga, H.; Nakano, M. (Isobe R&D Center, Gunma, Japan)  
 SO Japanese Journal of Applied Physics, Part 1 (Regular Papers, Short Notes & Review Papers) (March 1997) vol.36, no.3B, p.1646-9. 10 refs.  
 Published by: Publication Office, Japanese Journal Appl. Phys  
 CODEN: JAPNDE ISSN: 0021-4922  
 SICI: 0021-4922(199703)36:3BL.1646:EEPM;1-K  
 Conference: 1996 International Conference on Solid State Devices and Materials (SSDM'96). Yokohama, Japan, 26-29 Aug 1996  
 DT Conference Article; Journal  
 TC Experimental  
 CY Japan

LA English

L8 ANSWER 5 OF 8 INSPEC (C) 2005 IEE on STN

Full Text  Abstract  Citation

AN 1994:4825581 INSPEC DN A9501-6170-001  
 TI Modeling the energy of formation of defects of various dimensionalities in crystals of intermetallic compounds.  
 AU Starostenkov, M.D.; Dmitriev, S.V.; German, V.G. (Polzunov Altai State Univ., Barnaul, Russia)  
 SO Crystallography Reports (Sept.-Oct. 1994) vol.39, no.5, p.720-4. 6 refs.  
 Price: CCCC 1063-7745/94/3905-0720\$10.00  
 CODEN: CYSTE3 ISSN: 1063-7745  
 Translation of: Kristallografiya (Sept.-Oct. 1994) vol.39, no.5, p.798-802. 6 refs.  
 CODEN: KRISAJ ISSN: 0023-4761  
 DT Journal; Translation Abstracted  
 TC Theoretical  
 CY Russian Federation; Russian Federation  
 LA English

L8 ANSWER 6 OF 8 INSPEC (C) 2005 IEE on STN

Full Text  Abstract  Citation

AN 1993:4454228 INSPEC DN B9309-4360-005  
 TI Digital laser microscope for real-time defect imaging and review.  
 AU Worster, B.W. (Ultrapointe Corp., Santa Clara, CA, USA); Politzer, B.A.  
 SO Solid State Technology (May 1993) vol.36, no.5, p.55-6, 59. 2 refs.  
 CODEN: SSTEAP ISSN: 0038-111X  
 DT Journal  
 TC Application; Practical  
 CY United States  
 LA English

L8 ANSWER 7 OF 8 INSPEC (C) 2005 IEE on STN

Full Text  Abstract  Citation

AN 1990:3720088 INSPEC DN B90060830  
 TI Technique for failure analysis of tantalum capacitors.  
 AU Macdonald, M.A.; Brindel, F.; Sousa, D. (Sprague Electr. Co., Sanford, ME, USA)  
 SO 10th Capacitor and Resistor Technology Symposium. CARTS '90 Huntsville, AL, USA: Components Technol. Inst, 1990. p.29-34 of 208 pp. 3 refs.  
 Conference: San Francisco, CA, USA, 26-29 March 1990  
 Sponsor(s): Components Technol. Inst.; IEEE  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L8 ANSWER 8 OF 8 INSPEC (C) 2005 IEE on STN

Full Text  Abstract  Citation

AN 1990:3681141 INSPEC DN B90052141; C90051710  
 TI Algorithm for comparing fragments of images of two crystals for monitoring integrated circuit appearance.  
 AU Ivanov, V.A.; Kosykh, V.P.  
 SO Optoelectronics, Instrumentation and Data Processing (1989) no.2, p.29-34. 8 refs.

Price: CCCC 8756-6990/89/\$20.00  
 CODEN: OIDPE4 ISSN: 8756-6990  
 Translation of: Avtometriya (1989) no.2, p.29-34. 8 refs.  
 CODEN: AVMEBI ISSN: 0320-7102  
 DT Journal; Translation Abstracted  
 TC Application; Practical  
 CY USSR; United States  
 LA English

=> s d-defects  
 296296 D  
 116900 DEFECTS  
 L9 85 D-DEFECTS  
 (D(W)DEFECTS)

=> s l1 and l9  
 L10 7 L1 AND L9

=> d l10 1-7

L10 ANSWER 1 OF 7 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1998:6068361 INSPEC DN A9823-8110F-013; B9812-0510-026  
 TI D-defects and metal-related flow patterns.  
 AU Kissinger, G.; Morgenstern, G.; Richter, H. (Inst. fur Semicond. Phys., Frankfurt, Germany); Vanhellemont, J.; Graf, D.; Lambert, U.; Von Ammon, W.; Wagner, P.  
 SO Proceedings of the Symposium on Crystalline Defects and Contamination: Their Impact and Control in Device Manufacturing II  
 Editor(s): Kolbesen, B.O.; Claeys, C.; Stallhofer, P.; Tardiff, F.  
 Pennington, NJ, USA: Electrochem. Soc, 1997. p.32-9 of x+518 pp. 13 refs.  
 Conference: Paris, France, 31 Aug-5 Sept 1997  
 ISBN: 1-56677-175-7  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L10 ANSWER 2 OF 7 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1992:4065619 INSPEC DN A9204-6170B-002  
 TI Identification of vacancy clusters in FZ-Si crystals.  
 AU Kitano, T. (VLSI Dev. Div., NEC Corp., Kanagawa, Japan)  
 SO Physica Status Solidi A (16 Oct. 1991) vol.127, no.2, p.341-7. 16 refs.  
 CODEN: PSSABA ISSN: 0031-8965  
 DT Journal  
 TC Experimental  
 CY Germany, Federal Republic of  
 LA English

L10 ANSWER 3 OF 7 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1991:3945455 INSPEC DN A91104121  
 TI Behavior of point defects in FZ silicon crystals.  
 AU Abe, T.; Kimura, M. (Isobe R&D Center, Gunma, Japan)  
 SO Proceedings of the Sixth International Symposium on Silicon Materials

Science and Technology: Semiconductor Silicon 1990  
 Editor(s): Huff, H.R.; Barracough, K.G.; Chikawa, J.-I.  
 Pennington, NJ, USA: Electrochem. Soc, 1990. p.105-16 of xix+1090 pp. 23  
 refs.

Conference: Montreal, Que., Canada, 7-11 May 1990  
 Sponsor(s): Electrochem. Soc

DT Conference Article

TC Experimental

CY United States

LA English

L10 ANSWER 4 OF 7 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1988:3115574 INSPEC DN A88054503  
 TI Investigation of D defects in silicon by X-ray topography.  
 AU Vysotskaya, V.V.; Gorin, S.N.; Sorokin, L.M.; Sheikhett, E.G. (A.A. Baikov  
 Inst. of Metall., Acad. of Sci., Moscow, USSR)  
 SO Soviet Physics - Solid State (June 1987) vol.29, no.6, p.1068-70. 13 refs.  
 Price: CCCC 0038-5654/87/061068-03\$03.90  
 CODEN: SPSSA7 ISSN: 0038-5654  
 Translation of: Fizika Tverdogo Tela (June 1987) vol.29, no.6, p.1858-61.  
 13 refs.  
 CODEN: FTVTAC ISSN: 0367-3294  
 DT Journal; Translation Abstracted  
 TC Experimental  
 CY USSR; United States  
 LA English

L10 ANSWER 5 OF 7 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1987:2832599 INSPEC DN A87032340  
 TI Impurity effect on formation of microdefects during silicon crystal  
 growth.  
 AU Chikawa, J. (Nat. Lab. for High Energy Phys., Tsukuba, Japan)  
 SO Proceedings of the Fifth International Symposium on Silicon Materials  
 Science and Technology: Semiconductor Silicon 1986  
 Editor(s): Huff, H.R.; Abe, T.; Kolbesen, B.  
 Pennington, NJ, USA: Electrochem. Soc, 1986. p.61-75 of xiv+1096 pp. 27  
 refs.  
 Conference: Boston, MA, USA, 5-9 May 1986  
 Sponsor(s): Electrochem. Soc  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L10 ANSWER 6 OF 7 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1983:2139319 INSPEC DN A83113905  
 TI Microdefects and impurities in dislocation-free silicon crystals.  
 AU Abe, T.; Harada, H. (Shin-Etsu Handotai Co., Gunma-ken, Japan); Chikawa,  
 J.  
 SO Defects in Semiconductors II, Symposium Proceedings  
 Editor(s): Mahajan, S.; Corbett, J.W.  
 New York, NY, USA: North-Holland, 1983. p.1-17 of xv+582 pp. 26 refs.  
 Conference: Boston, MA, USA, Nov 1982  
 ISBN: 0-444-00812-8

DT Conference Article  
TC Experimental  
CY United States  
LA English

L10 ANSWER 7 OF 7 INSPEC (C) 2005 IEE on STN

Full Text References

AN 1983:2039012 INSPEC DN A83046938  
TI Swirl defects in float-zoned silicon crystals.  
AU Abe, T. (Shin-Etsu Handotai Co., Gunma-ken, Japan); Harada, H.; Chikawa, J.  
SO Physica B & C (Feb. 1983) vol.116B+C, no.1-3, p.139-47. 28 refs.  
Price: CCCC 0378-4363/83/0000-0000/\$03.00  
CODEN: PHBCDQ ISSN: 0378-4363  
Conference: Proceedings of the 12th International Conference on Defects in Semiconductors. Amsterdam, Netherlands, 31 Aug-3 Sept 1982  
Sponsor(s): IUPAP; European Phys. Soc.; Netherlands' Phys. Soc.; Univ. Amsterdam  
DT Conference Article; Journal  
TC Experimental  
CY Netherlands  
LA English

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